Non-uniform Distribution of Doped Carrier in a Na-doped CaB₆ Bulk Material Observed by EPMA-SXES

Masami Terauchi¹, Yohei Sato¹, Masatoshi Takeda², Tadashi Hatano¹, Masato Koike³, Hiroyuki Sasai⁴, Tetsuya Nagano⁴, Masaru Koeda⁴, Takanori Murano⁵ and Hideyuki Takahashi⁵

- ^{1.} Institute of Multidisciplinary Research for Advanced Materials, Tohoku University, Sendai, Japan.
- ² Materials Design and Engineering Group, Nagaoka University of Technology, Nagaoka, Japan.
- ³ QuBS Directorate, National Institute for Quantum and Radiological Science, Kizugawa, Japan.
- ^{4.} Device Department, SHIMADZU Corp., Kyoto, Japan.
- ^{5.} SA Business Unit, JEOL Ltd., Akishima, Japan.

Recently realized commercial X-ray fluorescence spectroscopy instrument for soft X-rays and extreme ultraviolet radiation, form 50 eV to 2000 eV, has a better or a comparable energy resolution with those of EPMA by using aberration corrected gratings and a two order better acquisition rate due to its parallel detection system by using a CCD detector [1,2]. Radiations in this energy range usually carry not only elemental but also chemical information, because those are generated by electronic transitions from valence bands (bonding electrons) to a shallow inner-shell core-hole state generated by an electron beam irradiation [3]. Here, EPMA-SXES (JXA-8230 with SS-94000SXES) study on a correlation between distributions of doped-atom and doped carrier in Na-doped CaB₆ bulk material is reported.

CaB₆ is a member of metal hexaboride MB₆ material, which is based on a network of B₆-clusters. When an M atom can supply two electrons to B₆-network, the valence bands (VB) of B₆-network is fully occupied and becomes a *n*-type semiconductor as in the case of CaB₆ [4]. For producing a *p*-type character CaB₆, Na-doping had been conducted and succeeded [5]. EDS analysis of the *p*-type CaB₆ showed an inclusion of a few % of Na. Doped Na atoms occupy Ca site. As one Na atom can transfer one electron to B₆-network, Na-doping can be a hole-doping based on the rigid band-structure scheme.

Figure 1 shows (a) secondary electron (SE) image, (b) Ca-Ll, η intensity (150-154 eV) map, (c) B-K intensity (170-188 eV) map and (d) map of the top part of B-K intensity (187-188 eV) which corresponds to the top of the valence band. In the SE image, a contamination in the upper left region is only noticed. The area showed carbon K-emission intensity, not shown here. The Ca-Ll, η intensity map of (b) shows a non-uniformity in Ca atom distribution. As doped Na-atoms occupy Ca-atom sites, the Ca-deficient region observed should be a highly Na-substituted region. Unfortunately, X-ray emission signal from Na atoms cannot be detected with the present spectrometer. B K-emission intensity of (c) shows a little decrease in the Na-substituted region. On the other hand, the map of the top part of B-K intensity of (d) shows an intensity in this region. B K-emission spectrum of the Na-doped region showed a little different intensity distribution compared to that of surrounding region. Furthermore, the spectrum shift in higher energy side was also noticed. Thus, the intensity increase in (d) can be understood as a shift of B K-emission intensity in higher energy side due to a larger binding energy of B 2p level, chemical shift, caused by the hole doping for B₆-cluster network. The observed localization of doped carrier in (d) may be reasonable owing to a charge compensation of doped Na-atoms.

This experimental result shows that the high energy-resolution soft X-ray mapping with an appropriate energy window can show not only elemental distribution but also chemical state distribution or doped carrier distribution of bulk materials [6].

- [1] H Takahashi *et al*, Microscopy and Microanalysis **20**(Suppl 3) (2014) p.684.
- [2] H Takahashi et al, Abstract of EMAS 2017/IUMAS-7 (2017) p.458.
- [3] M Terauchi in "Valence electron spectroscopy for transmission electron microscopy", ed. by CSSR Kumar (Springer-Verlag, Berlin Heidelberg, 2014) p. 287.
- [4] M Takeda et al., J. Solid State Chemistry 179 (2006) p.2823.
- [5] H Kuribayashi, S Makino and M Takeda, Abstract of ISBB-18 (2014) p.148.
- [6] This work was partly supported by the Research Program of "Dynamic Alliance for Open Innovation Bridging Human, Environment and Materials" in "Network Joint Research Centre for Materials and Devices".

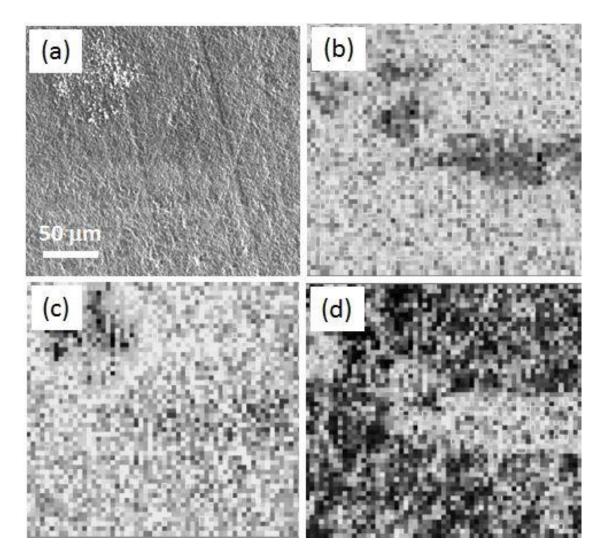


Figure 1. (a) secondary electron image of Na-doped CaB₆ bulk specimen. (b) Ca-Ll, η emission intensity map. (c) B-K emission intensity map. (d) B-K emission intensity setting an energy window at the top region of the spectra.